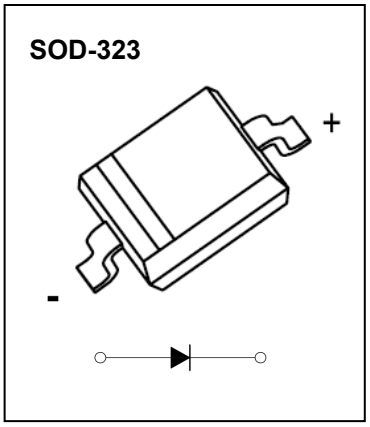
SOD-323 Plastic-Encapsulate Diodes



FEATURES

- Low Forward Voltage Drop
- Guard Ring Construction for Transient Protection
- High Conductance
- Also Available in Lead Free Version

MARKING:SE



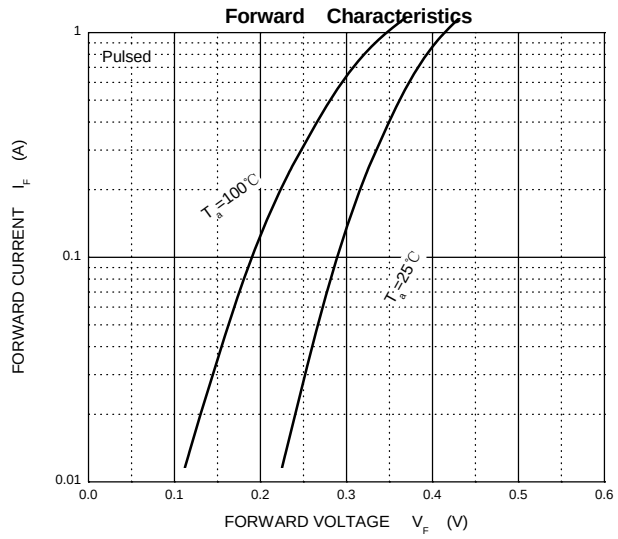
Maximum Ratings @Ta=25℃

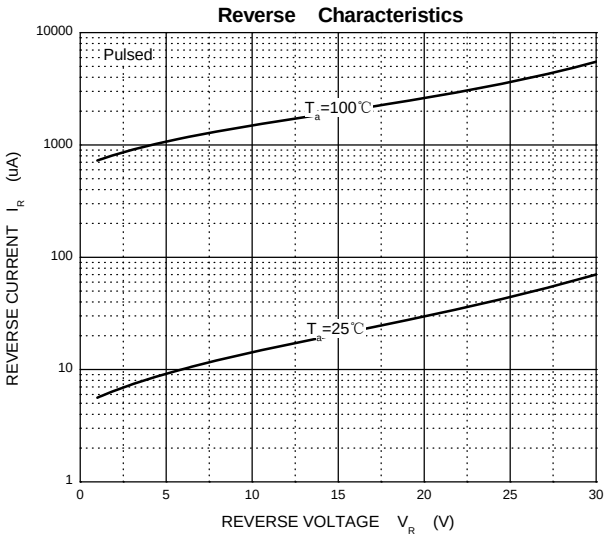
Parameter	Symbo	Value	Unit
Peak repetitive peak reverse voltage **Working peak reverse voltage** **DC blocking voltage**	V_{RRM} V_{RWM} V_R	30	V
RMS reverse voltage reverse voltage (DC)	$V_{R(RMS)}$	21	V
Average rectified output current	I_o	0.5	A
Non-repetitive Peak Forward Surge Current @t=8.3ms	I_{FSM}	5.5	A
Power dissipation	P_D	200	mW
Thermal resistance junction to ambient	$R_{\theta JA}$	500	℃/W
Junction temperature	T_j	125	℃
Storage temperature	T_{STG}	-55~+150	℃
Voltage rate of change	dv/dt	1000	V/μs

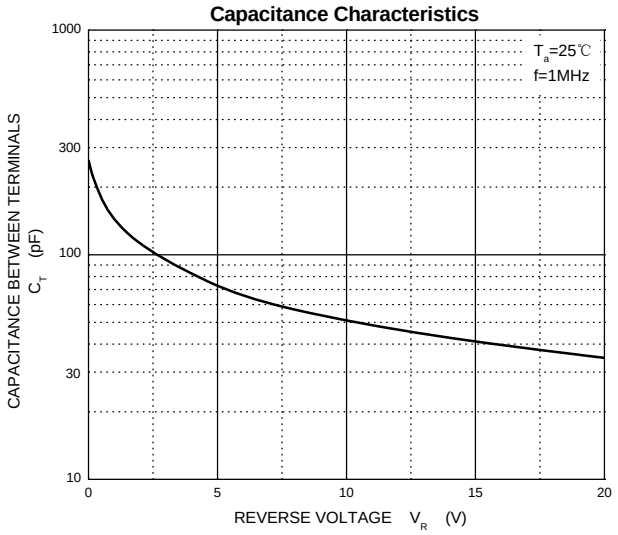
Electrical Characteristics @Ta=25℃

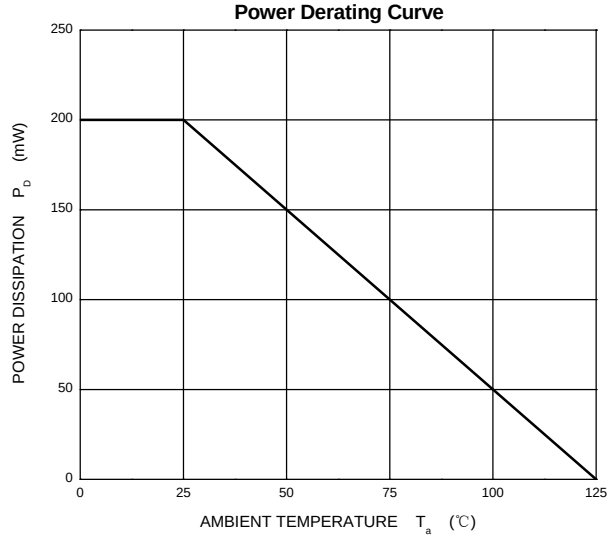
	Symbol	Test conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	$V_{(BR)}$	I_R=500uA	30			V
Reverse current	I_R	V_R=15V			80	uA
		V_R=20V			100	
		V_R=30V			500	
Forward voltage	V_F	I_F=0.1A			0.36	V
		I_F=0.5A			0.45	
Capacitance between terminals	C_T	V_R=1,f=1MHz		170		pF

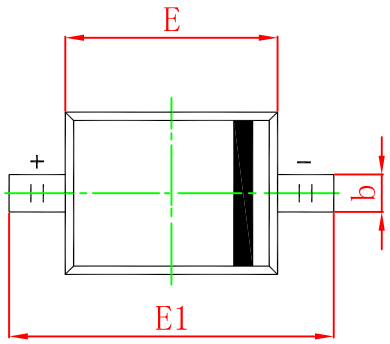
Typical Characteristics

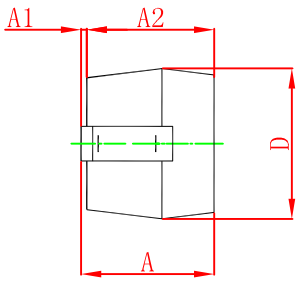


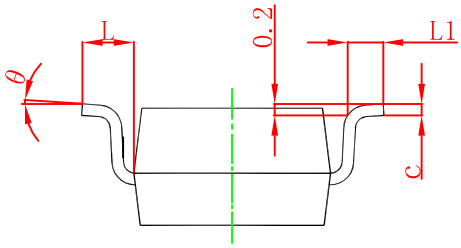






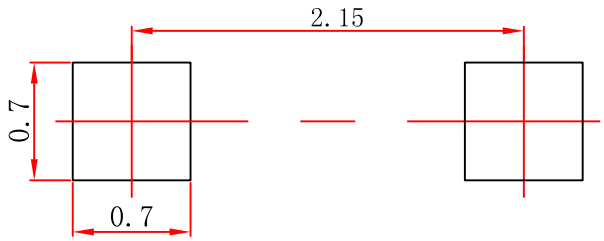






Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A		1.000		0.039
A1	0.000	0.100	0.000	0.004
A2	0.800	0.900	0.031	0.035
b	0.250	0.350	0.010	0.014
c	0.080	0.150	0.003	0.006
D	1.200	1.400	0.047	0.055
E	1.600	1.800	0.063	0.071
E1	2.550	2.750	0.100	0.108
L	0.475 REF.		0.019 REF.	
L1	0.250	0.400	0.010	0.016
θ	0°	8°	0°	8°

SOD-323 Suggested Pad Layout



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:±0.05mm.
3.The pad layout is for reference purposes only.